

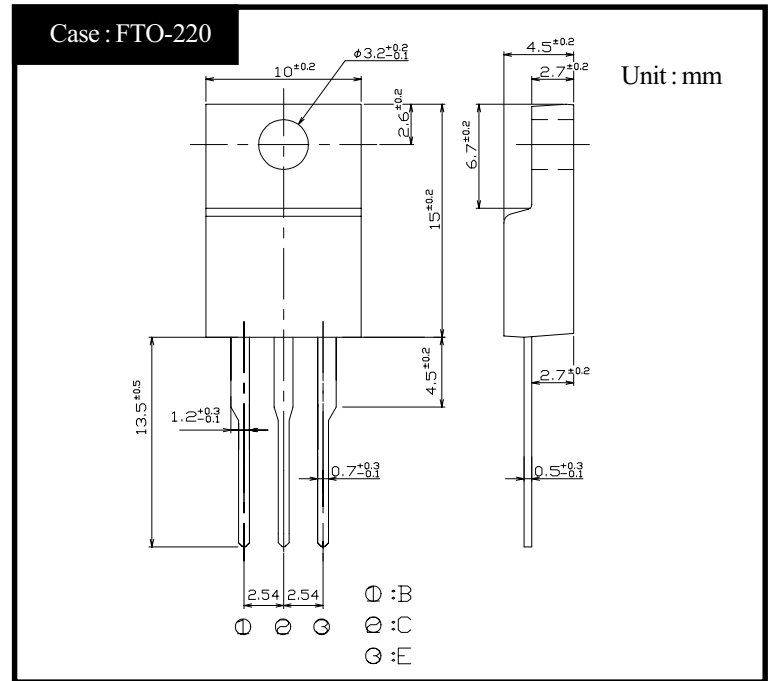
SHINDENGEN

Switching Power Transistor

2SC5382

6A NPN

OUTLINE DIMENSIONS



RATINGS

● Absolute Maximum Ratings

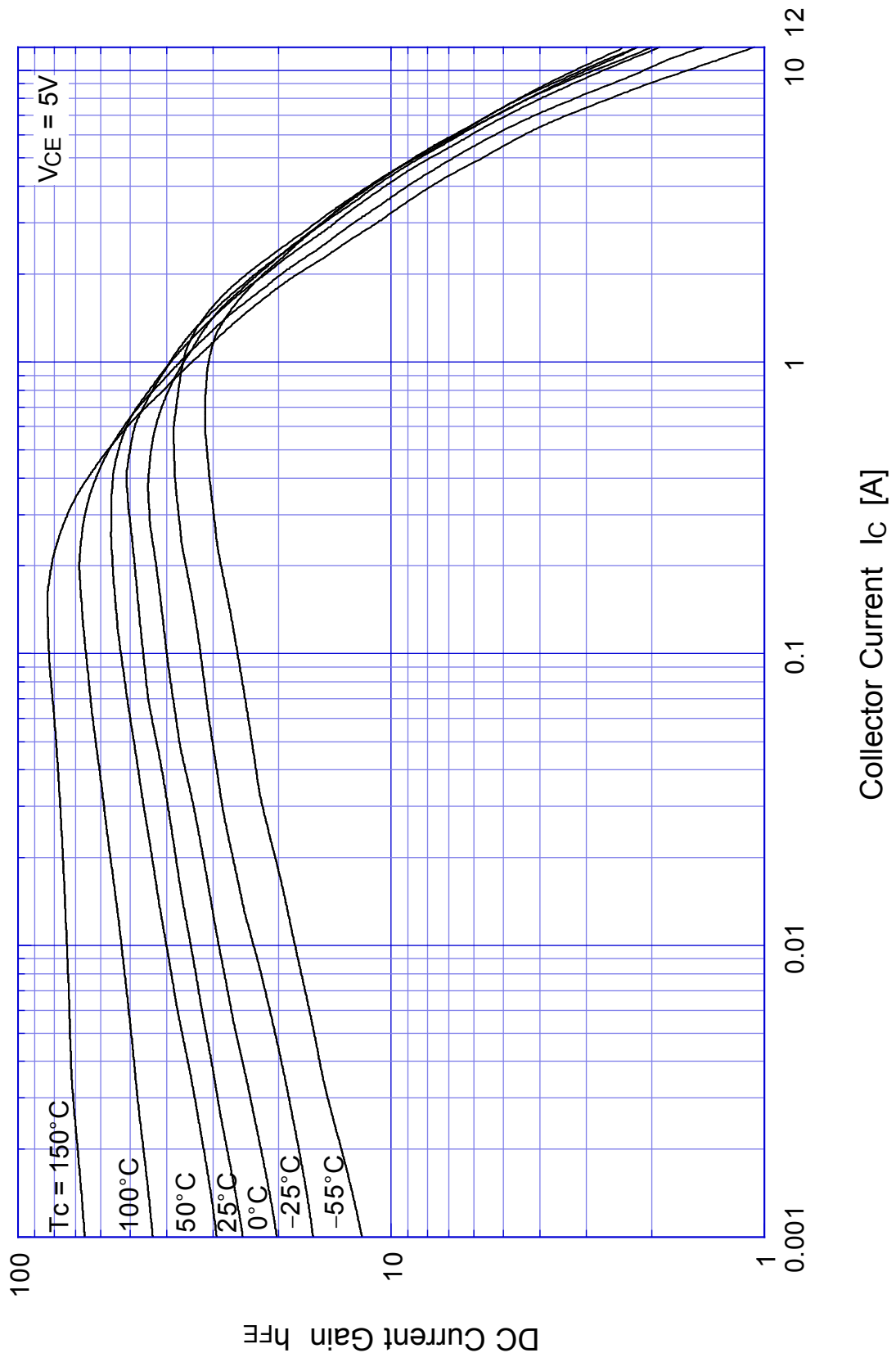
Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T_{stg}		-55 ~ 150	°C
Junction Temperature	T_j		150	°C
Collector to Base Voltage	V_{CBO}		1200	V
Collector to Emitter Voltage	V_{CEO}		550	V
Emitter to Base Voltage	V_{EBO}		9	V
Collector Current DC	I_C		6	A
Collector Current Peak	I_{CP}		12	
Base Current DC	I_B		3	A
Base Current Peak	I_{BP}		6	
Total Transistor Dissipation	P_T		40	W
Dielectric Strength	V_{dis}	Terminals to case, AC 1 minute	2	kV
Mounting Torque	TOR	(Recommended torque)	0.5(0.3)	N·m

● Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Conditions	Ratings	Unit
Collector to Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 0.1A$	Min 550	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 1200V$	Max 0.1	mA
	I_{CEO}	$V_{CE} = 550V$	Max 0.1	
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 9V$	Max 0.1	mA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 3A$	Min 10	
	h_{FEL}	$V_{CE} = 5V, I_C = 1mA$	Min 10	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 3A$	Max 1.0	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_B = 0.6A$	Max 1.5	V
Thermal Resistance	θ_{jc}	Junction to case	Max 3.13	°C/W
Turn on Time	t_{on}	$I_C = 3A$	Max 1.3	μs
Storage Time	t_s	$I_{B1} = 0.6A, I_{B2} = 1.2A$	Max 4.0	
Fall Time	t_f	$R_L = 50\Omega, V_{BB2} = 4V$	Max 0.3	

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$h_{FE} - I_C$

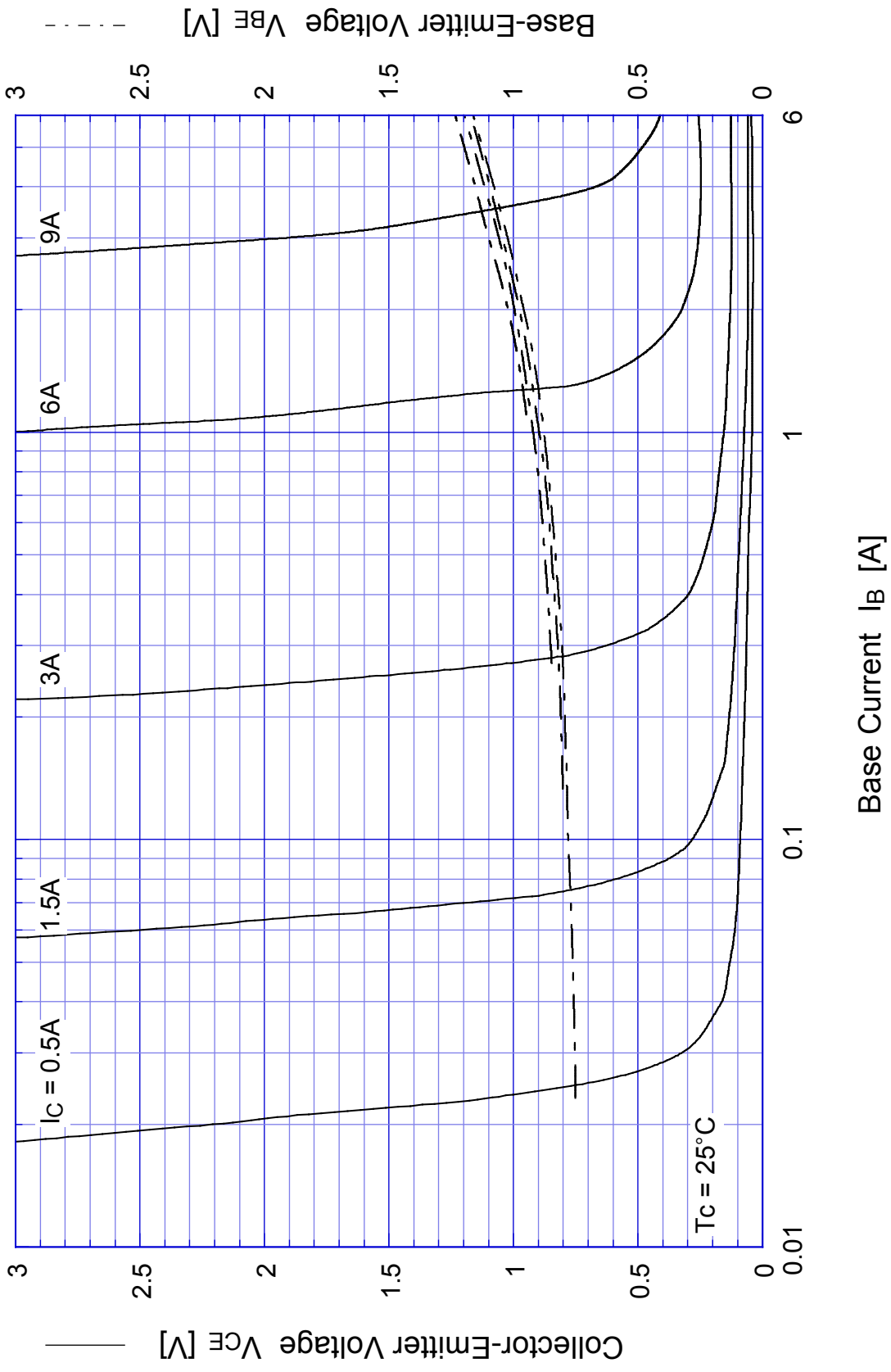


$V_{CE} = 5V$

DC Current Gain h_{FE}

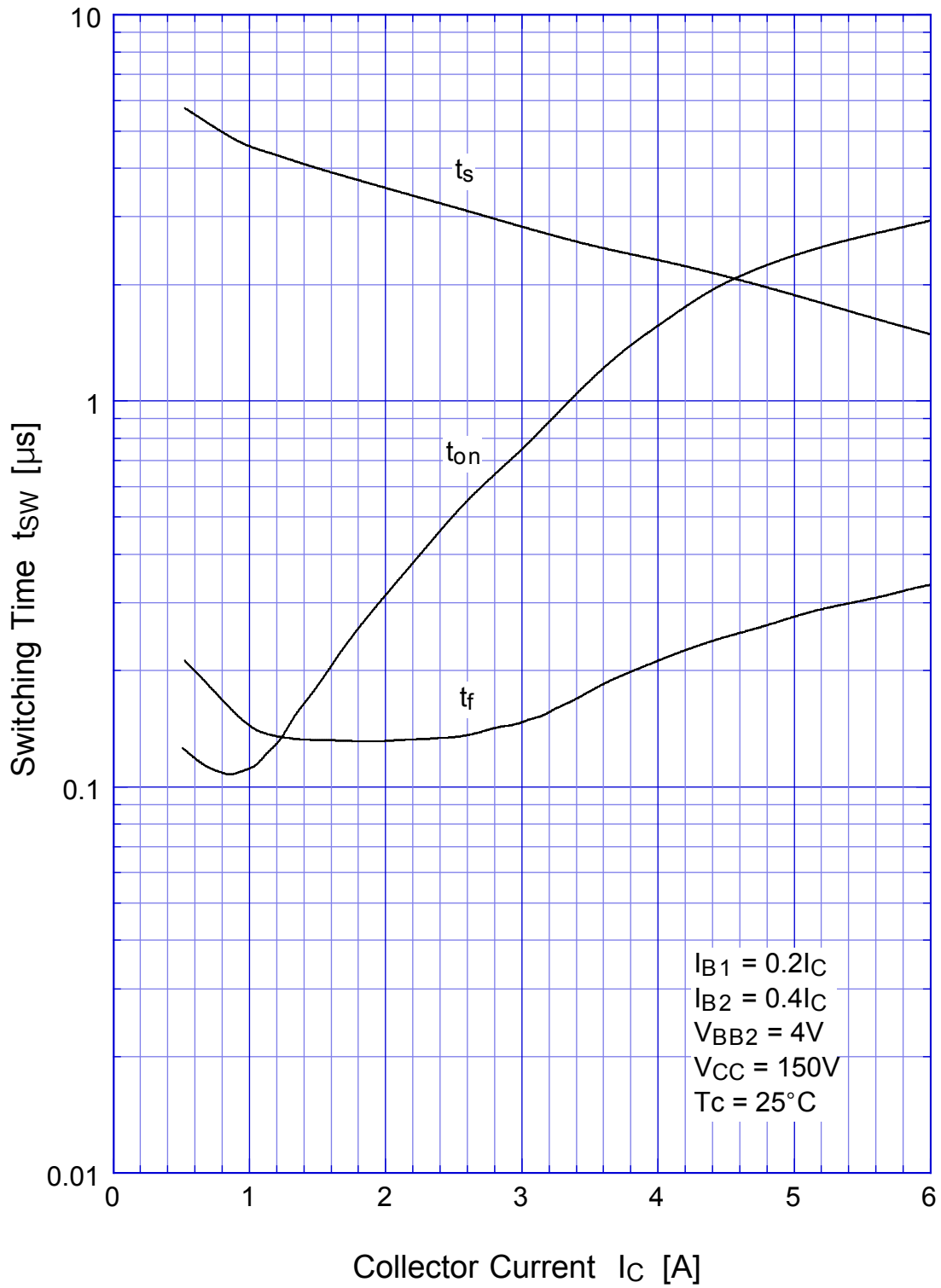
Collector Current I_C [A]

2SC5382 Saturation Voltage

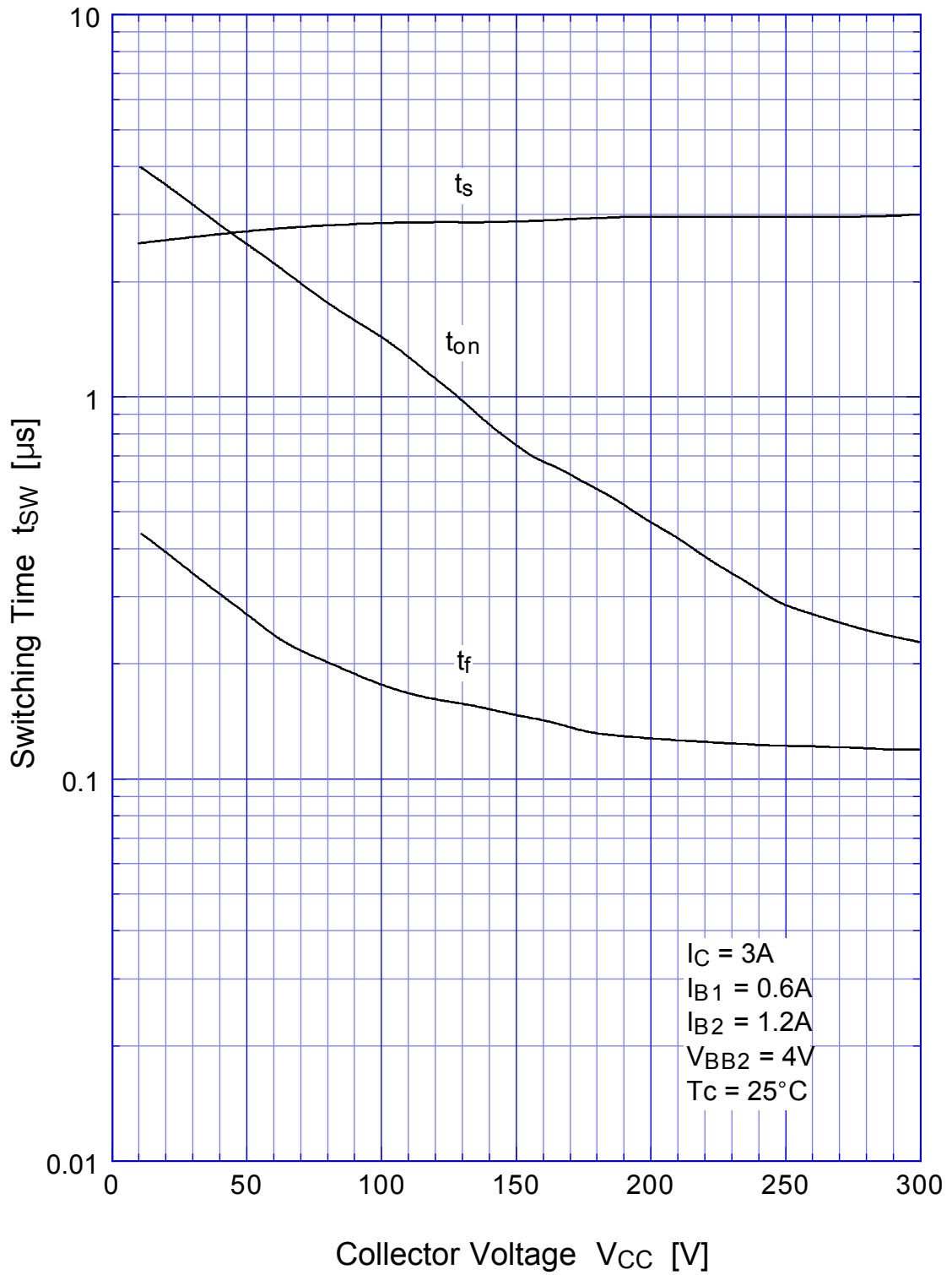


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Switching Time - I_C

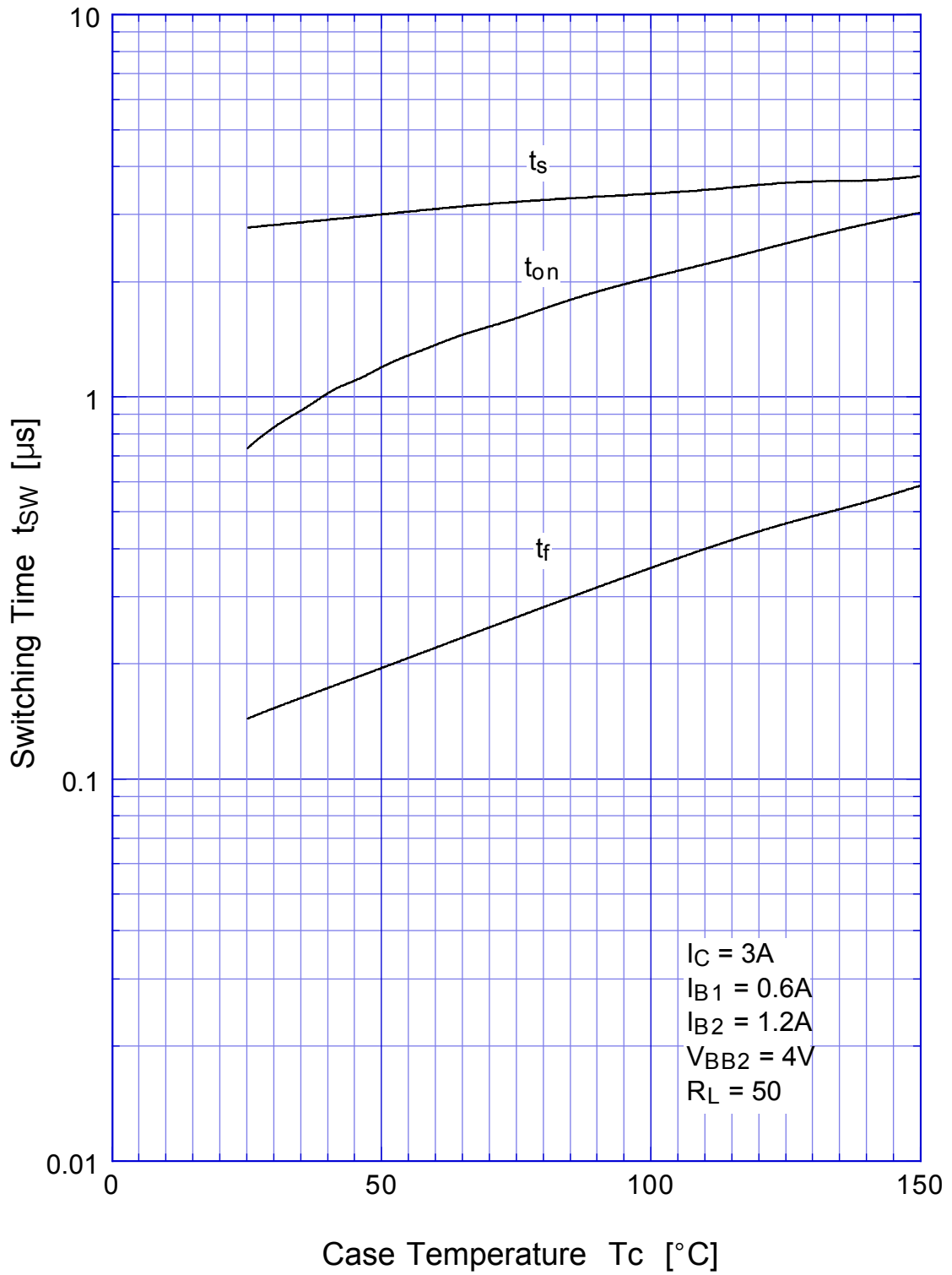


2SC5382 Switching Time - V_{CC}

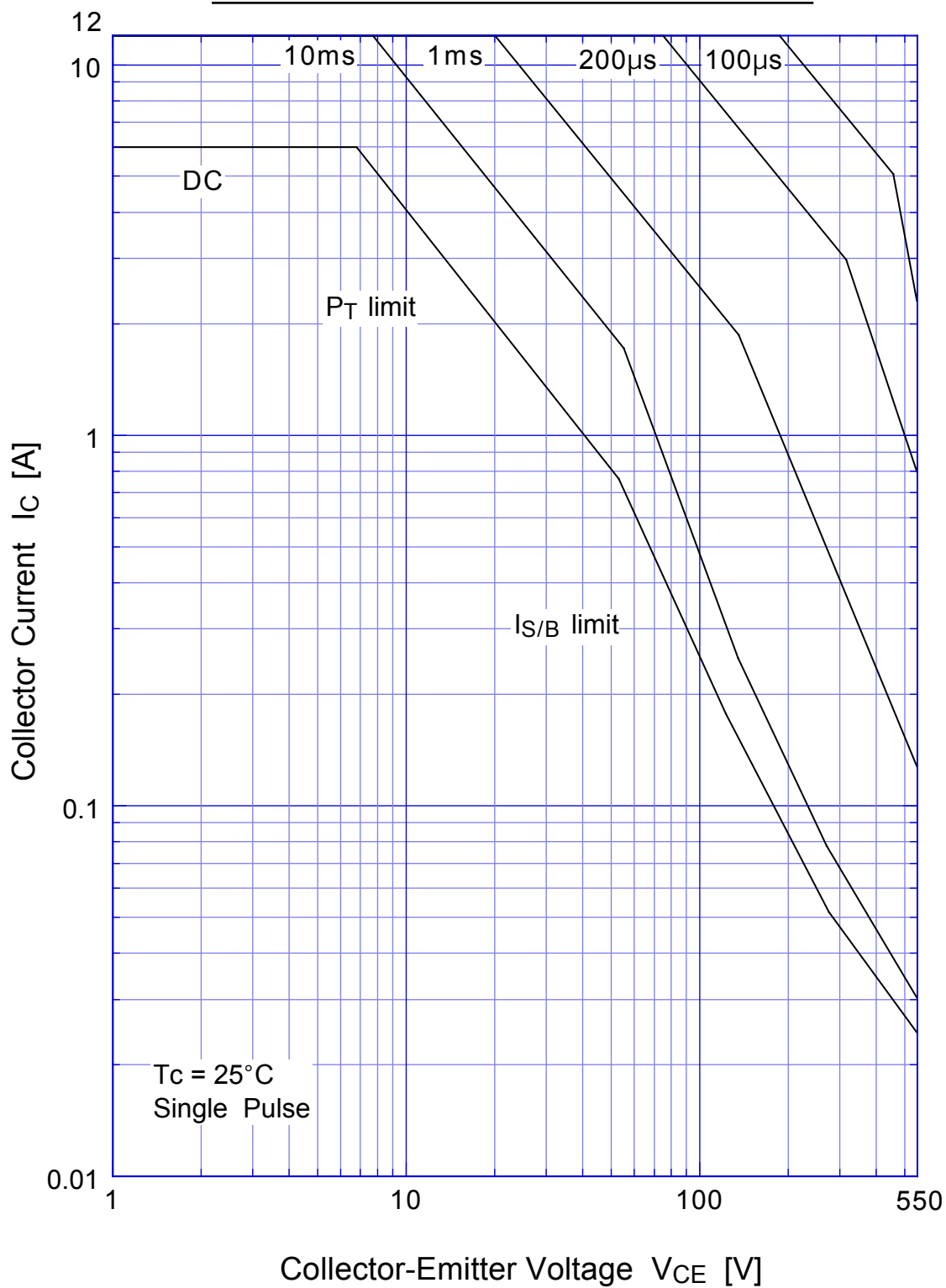


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Switching Time - Tc



2SC5382 Forward Bias SOA

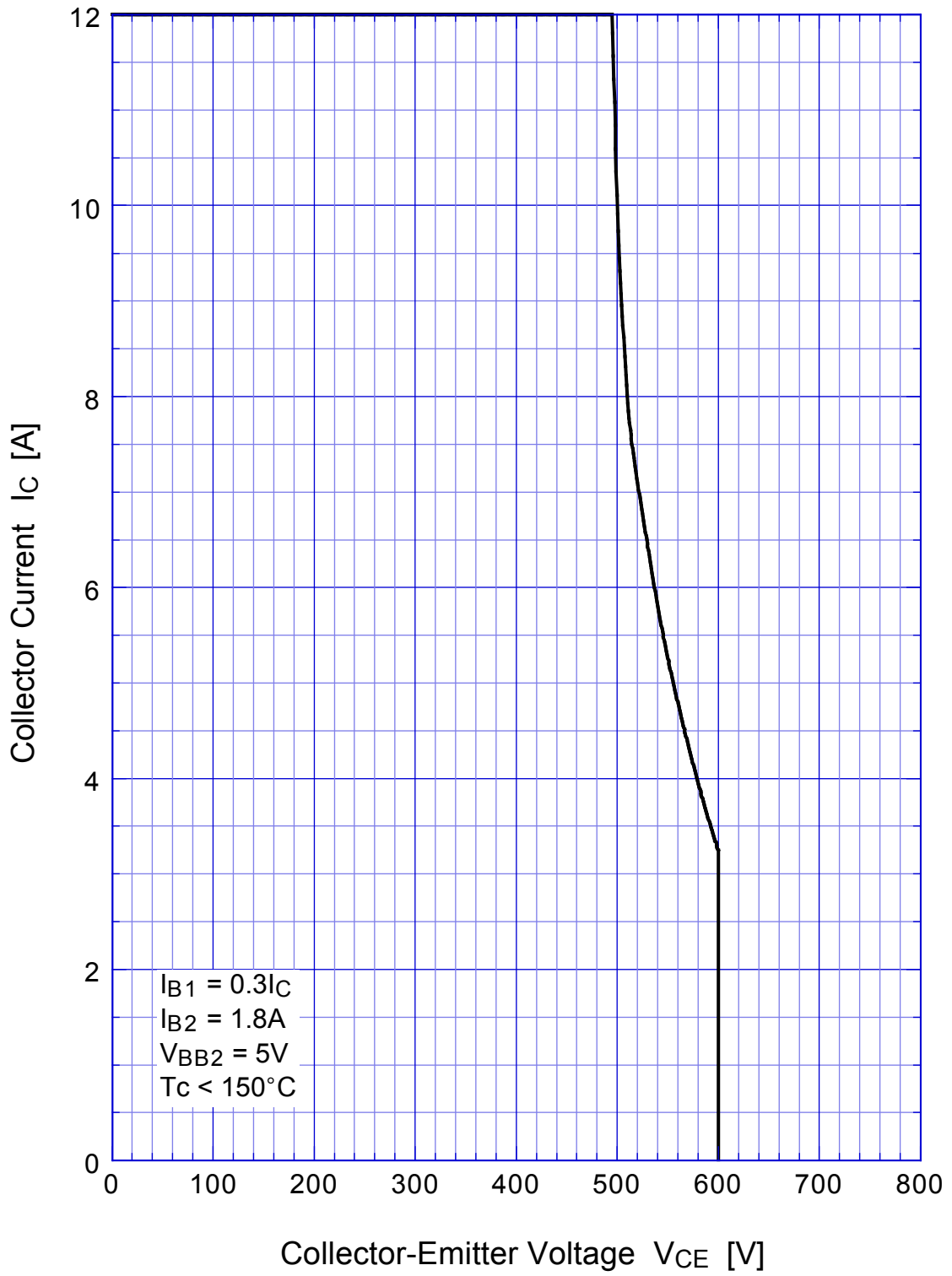


2SC5382 Collector Current Derating



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Reverse Bias SOA



2SC5382 Transient Thermal Impedance

